

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2N6263 2N6264

DESCRIPTION

- With TO-66 package
- High breakdown voltage
- Low collector saturation voltage

APPLICATIONS

- A wide variety of medium-to-high power, high-voltage applications
- Series and shunt regulators
- High-fidelity amplifiers
- Power switching circuits
- Solenoid drivers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

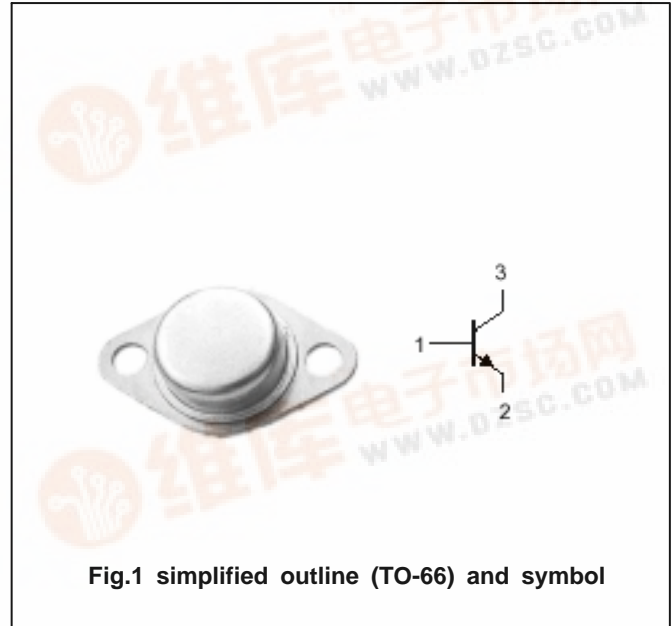


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6263	140	V
		2N6264	170	
V _{CEO}	Collector-emitter voltage	2N6263	120	V
		2N6264	150	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		3	A
I _{CM}	Collector current-peak		4	A
I _B	Base current		2	A
P _T	Total power dissipation	2N6263	20	W
		2N6264	50	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	2N6263	8.75
		2N6264	3.5



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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6263	I _C =0.1 A ; I _B =0			V
		2N6264				
V _{CEsat}	Collector-emitter saturation voltage	2N6263	I _C =0.5A ; I _B =0.05A			V
		2N6264	I _C =1.0A ; I _B =0.1A			
V _{BE}	Base -emitter on voltage	2N6263	I _C =0.5A ; V _{CE} =4V			V
		2N6264	I _C =1.0A ; V _{CE} =2V			
I _{CEX}	Collector cut-off current	2N6263	V _{CE} =120V ; V _{BE(off)} =-1.5V T _C =150			mA
		2N6264	V _{CE} =150V ; V _{BE(off)} =-1.5V T _C =150			
I _{CEO}	Collector cut-off current	2N6263	V _{CE} =100V ; I _B =0			mA
		2N6264	V _{CE} =130V ; I _B =0			
I _{EBO}	Emitter cut-off current	2N6263	V _{EB} =5V ; I _C =0			mA
		2N6264	V _{EB} =7V ; I _C =0			
h _{FE-1}	DC current gain	2N6263	I _C =0.5 A ; V _{CE} =4V			
		2N6264	I _C =1A ; V _{CE} =2V			
h _{FE-2}	DC current gain	2N6263	I _C =3A ; V _{CE} =2V			
		2N6264				
f _T	Transition frequency	I _C =0.2A ; V _{CE} =4V	200			KHz
I _{S/b}	Second breakdown collector current with base forward biased	2N6263	V _{CE} =120Vdc, t=1.0s, Nonrepetitive			A
		2N6264				

PACKAGE OUTLINE

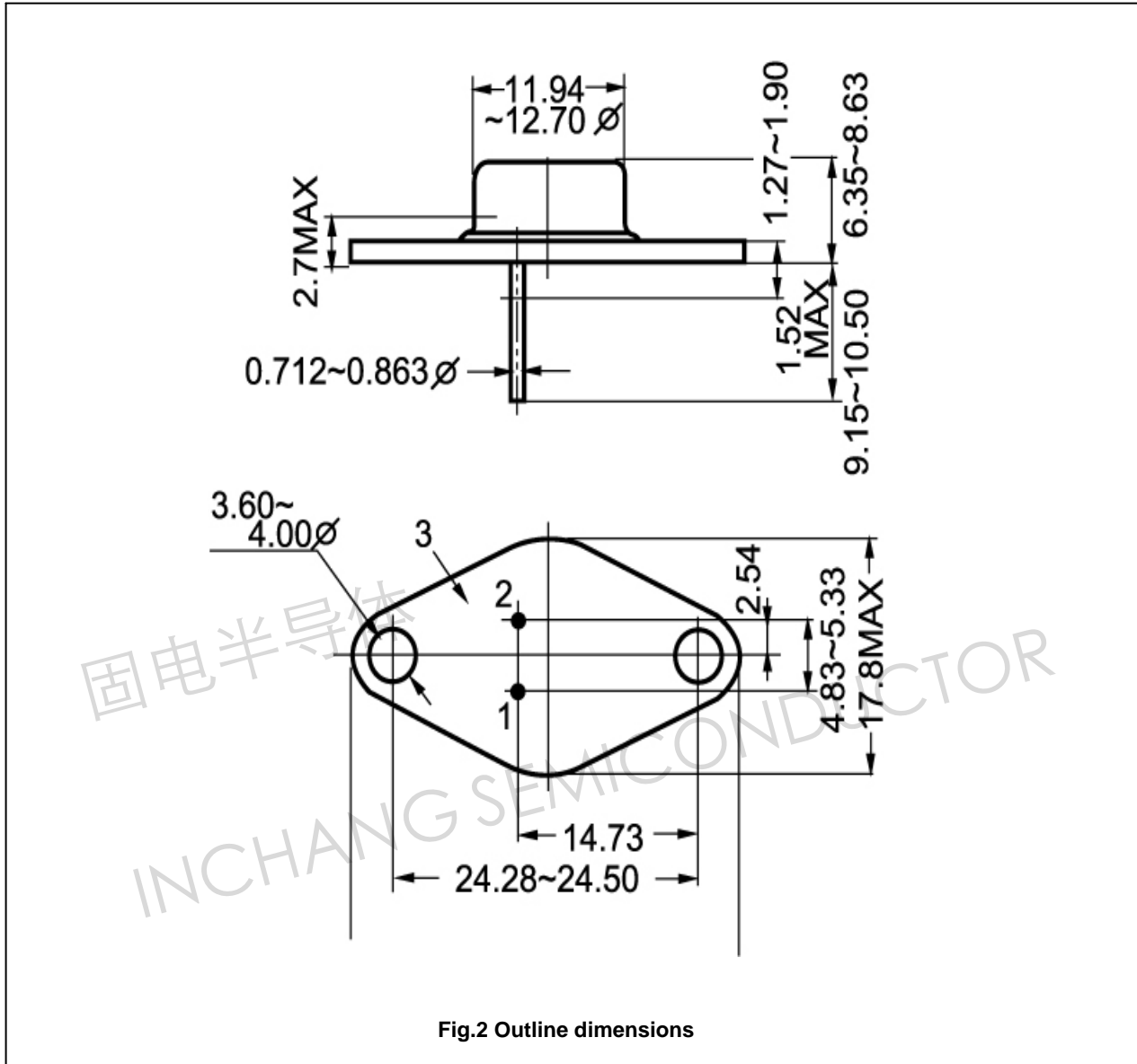


Fig.2 Outline dimensions